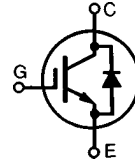


# HiPerFAST™ IGBT with Diode

## IXGK 50N60AU1

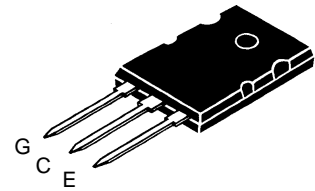
$V_{CES} = 600 \text{ V}$   
 $I_{C25} = 75 \text{ A}$   
 $V_{CE(sat)} = 2.7 \text{ V}$   
 $t_{fi} = 275 \text{ ns}$

### Combi Pack



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$ , limited by leads	75	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	50	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	200	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 10 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 100$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque (M4)	0.9/6	Nm/lb.in.
<b>Weight</b>		10	g
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$

TO-264 AA



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

### Features

- International standard package JEDEC TO-264 AA
- High frequency IGBT and anti-parallel FRED in one package
- 2nd generation HDMOS™ process
- Low  $V_{CE(sat)}$  - for minimum on-state conduction losses
- MOS Gate turn-on - drive simplicity
- Fast Recovery Epitaxial Diode (FRED) - soft recovery with low  $I_{RM}$

### Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

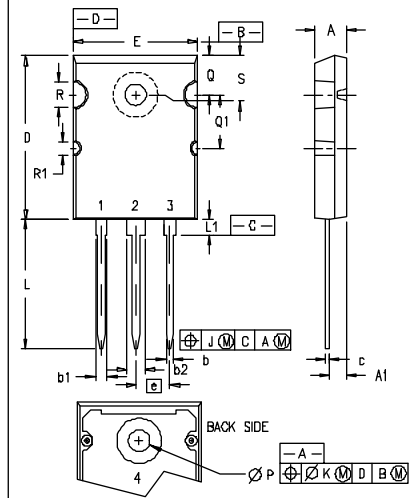
### Advantages

- Space savings (two devices in one package)
- Easy to mount with 1 screw (isolated mounting screw hole)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 500 \mu\text{A}$ , $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 500 \mu\text{A}$ , $V_{CE} = V_{GE}$	2.5		5.5 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			250 $\mu\text{A}$ 15 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$			2.7 V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	25	35	S
$Q_g$	$I_C = I_{C90}$ ; $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		200	nC
$Q_{ge}$			50	nC
$Q_{gc}$			80	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b>		50	ns
$t_{ri}$	$I_C = I_{C90}$ ; $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ ; $R_G = R_{off} = 2.7\ \Omega$		210	ns
$t_{d(off)}$	Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		200	ns
$t_{fi}$			275	400 ns
$E_{off}$			4.8	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b>		50	ns
$t_{ri}$	$I_C = I_{C90}$ ; $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$		240	ns
$E_{on}$	$V_{CE} = 0.8 V_{CES}$ ; $R_G = R_{off} = 2.7\ \Omega$		3	mJ
$t_{d(off)}$	Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		280	ns
$t_{fi}$			600	ns
$E_{off}$			9.6	mJ
$R_{thJC}$				0.42 K/W
$R_{thCK}$		0.15		K/W

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = I_{C90}$ ; $V_{GE} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.7 V
$I_{RM}$	$I_F = I_{C90}$ ; $V_{GE} = 0\text{ V}$ , $-di_F/dt = 480\text{ A}/\mu\text{s}$ $V_R = 360\text{ V}$ $T_J = 125^\circ\text{C}$ $I_F = 1\text{ A}$ ; $-di/dt = 200\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$ $T_J = 25^\circ\text{C}$		19	33 A
$t_{rr}$			175	ns
			35	50 ns
$R_{thJC}$				0.75 K/W

**TO-264 AA Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
$\varnothing P$	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
$\varnothing R$	.155	.187	3.94	4.75
$\varnothing R1$	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

- 1 - GATE  
2, 4 - DRAIN (COLLECTOR)  
3 - SOURCE (EMITTER)

Fig. 1 Saturation Characteristics

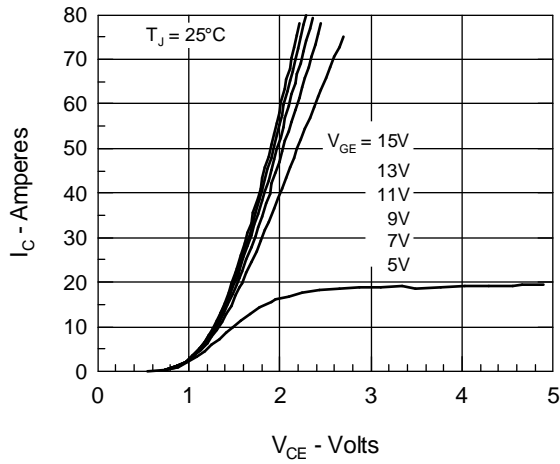


Fig. 2 Output Characteristics

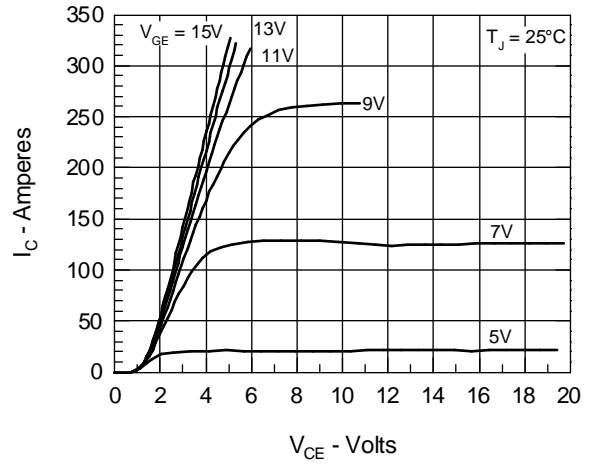


Fig. 3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

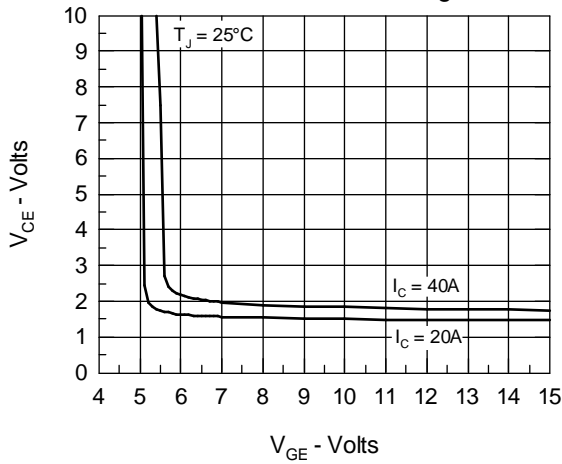


Fig. 4 Temperature Dependence of Output Saturation Voltage

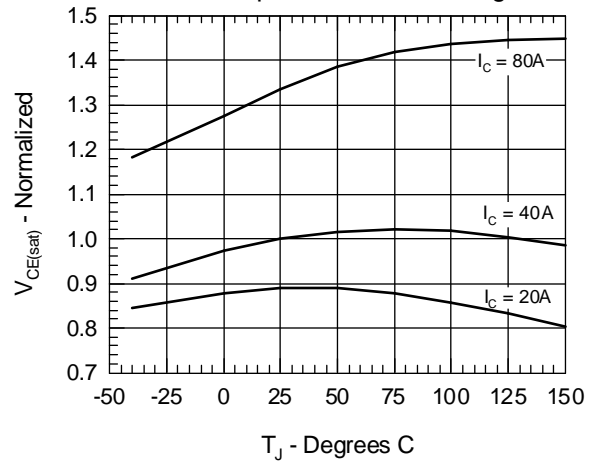


Fig. 5 Input Admittance

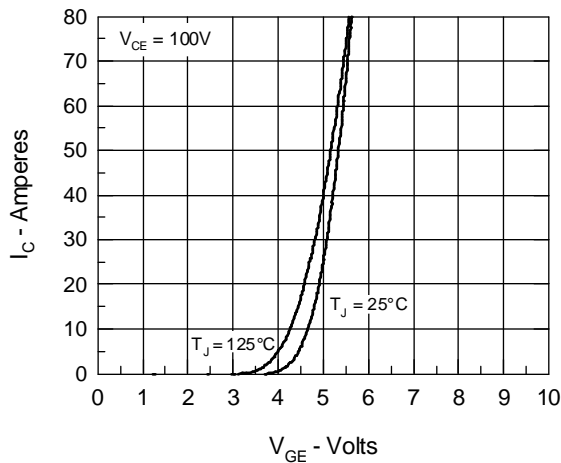


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

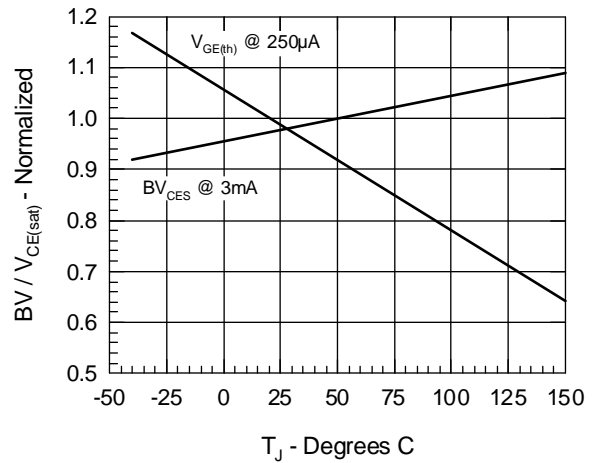


Fig.7 Gate Charge

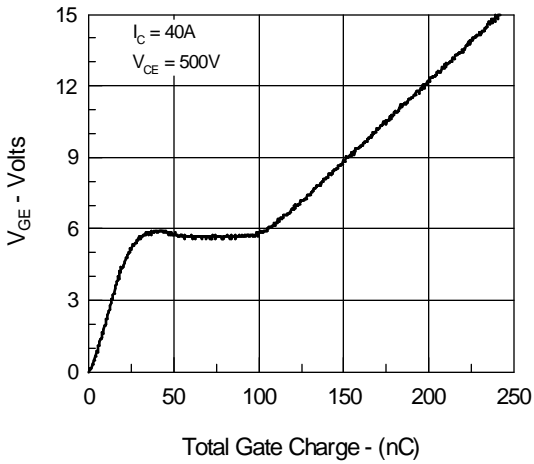


Fig.8 Turn-Off Safe Operating Area

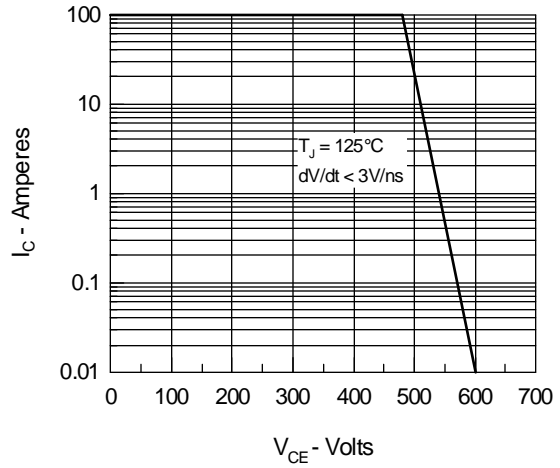


Fig.9 Capacitance Curves

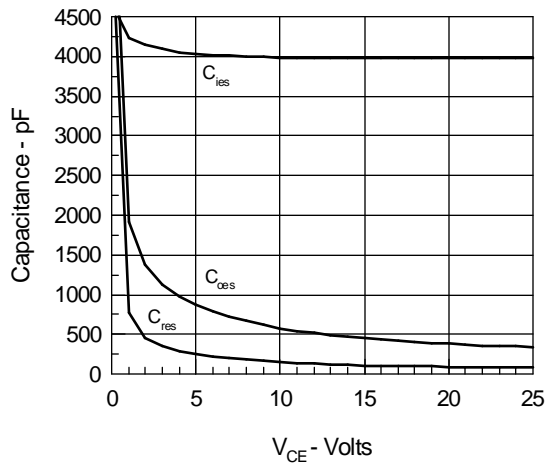
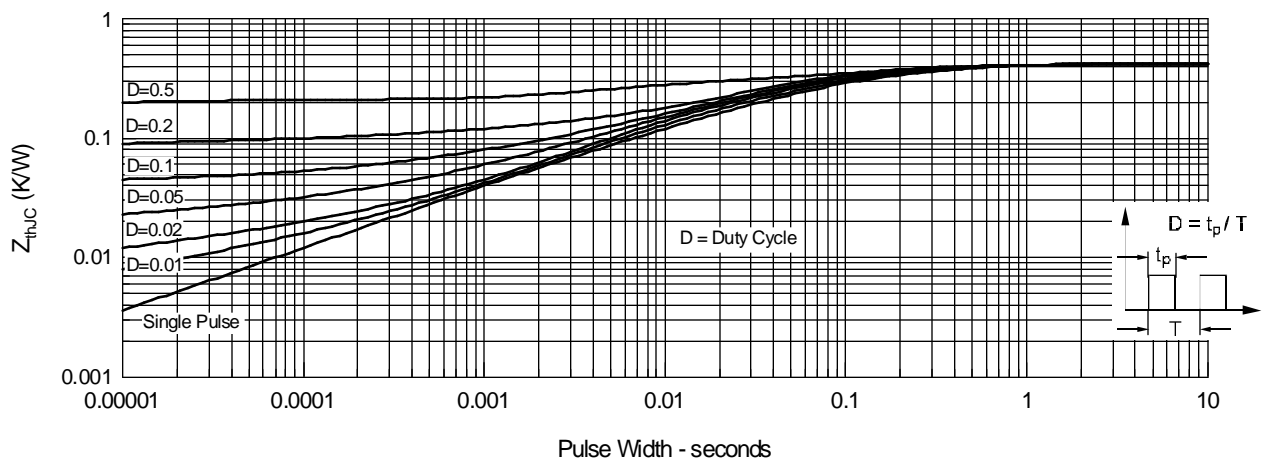


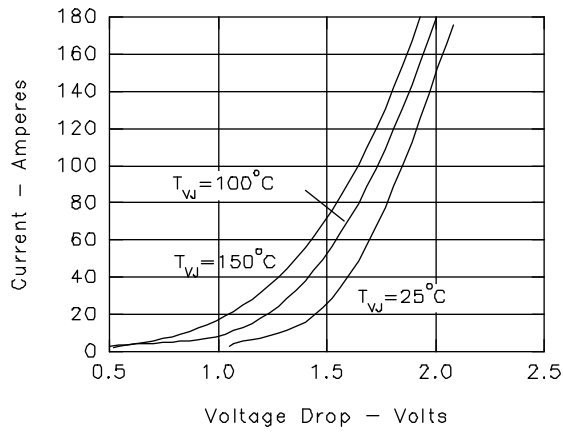
Fig.10 Transient Thermal Impedance



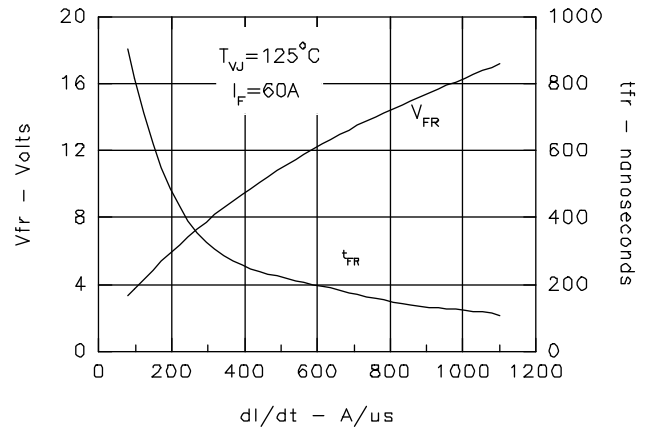
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

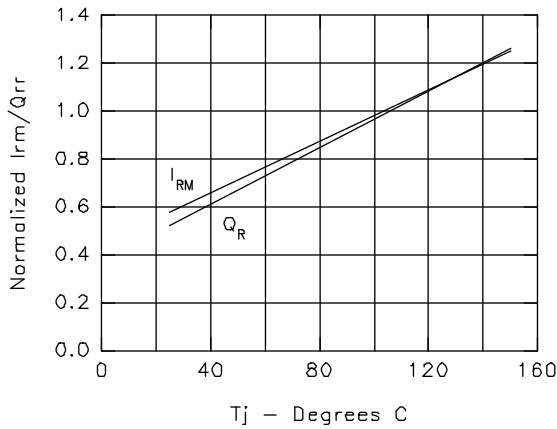
**Fig. 12. Maximum Forward Voltage Drop**



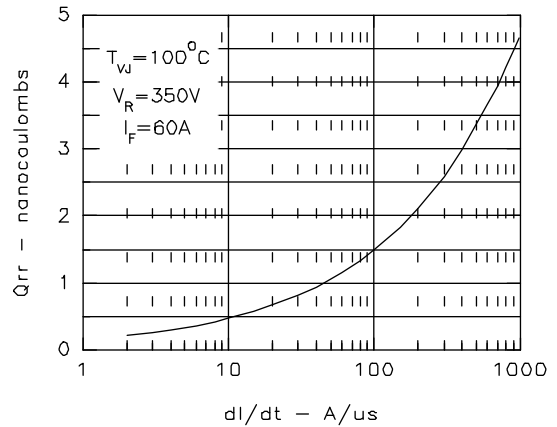
**Fig. 13. Peak Forward Voltage  $V_{FR}$  and Forward Recovery Time  $t_{FR}$**



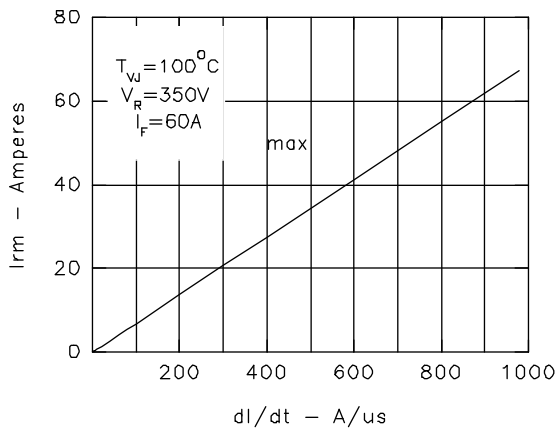
**Fig. 14. Junction Temperature Dependence of  $I_{RM}$  and  $Q_R$**



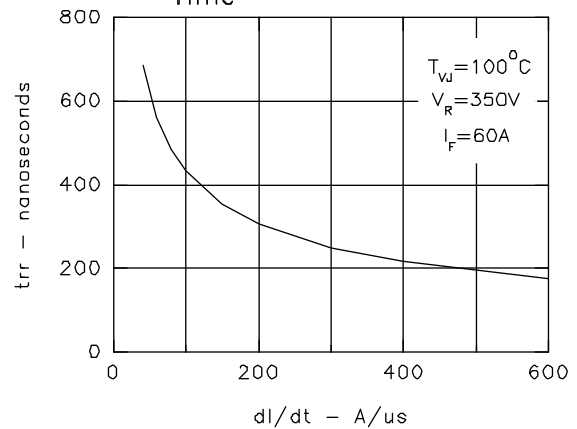
**Fig. 15. Maximum Reverse Recovery Charge**



**Figure 16. Peak Reverse Recovery Current.**



**Fig. 17. Maximum Reverse Recovery Time**



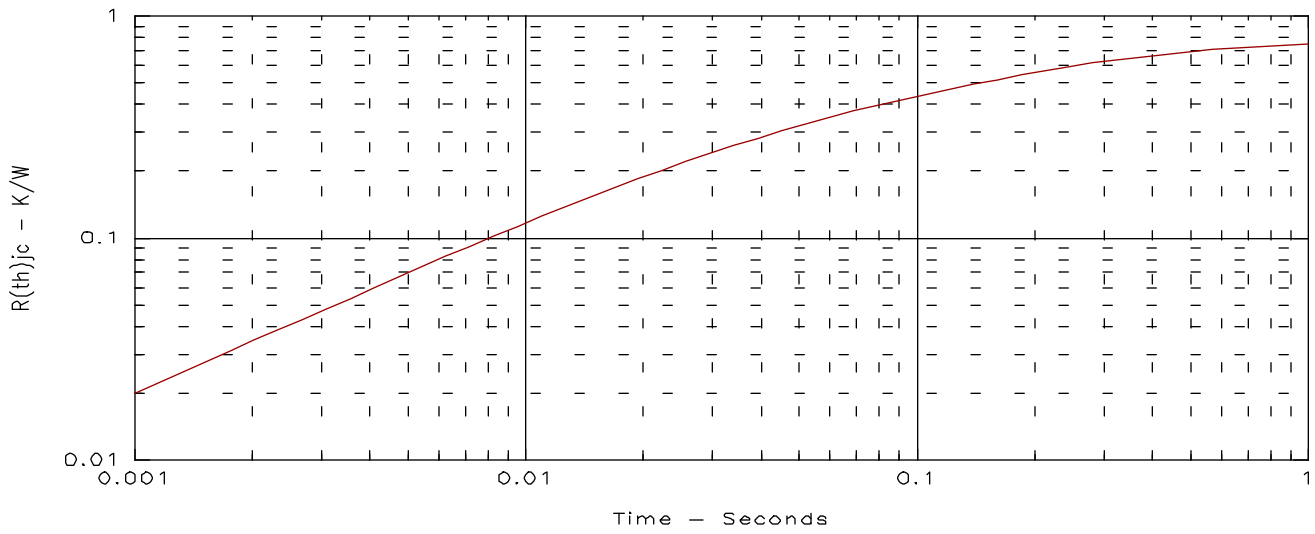


Fig. 18. Diode transient thermal resistance junction-to-case.